

[Document Name] ABSTRACT

[Abstract]

[Problem] The object is to provide a semiconductor
production apparatus including an improved susceptor
5 as a wafer support and an improved susceptor supporting
shaft, which can yield an epitaxially grown silicon
film having a substantially uniform thickness.

[Means of Solution] An epitaxial growth apparatus
10A is of a single wafer processing type, which
10 processes semiconductor wafers or silicon wafers W
one by one, and comprises a process chamber 12 of silica
glass and a susceptor 14A disposed within the process
chamber 12 for supporting a silicon wafer W as
semiconductor wafer. The susceptor 14A is supported
15 and positioned by the shaft 15A at only the peripheral
portion in the lower surface thereof. A side portion
of the process chamber 12 is formed with an inlet 16
for a process gas. Also, a side portion of the process
chamber 12 is formed with an outlet 18 at a position
20 opposite from the inlet 16. A plurality of halogen
lamps 20 are radially disposed with an appropriate
arrangement in each of areas above and below the
process chamber 12.

[Selected Drawing] Fig. 1

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